

L Number	Hits	Search Text	DB	Time stamp
1	230	rtcvd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/13 13:22
8	76316	ono	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/13 13:22
15	1152	cluster adj tool	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/13 13:23
22	2	rtcvd and ono and (cluster adj tool)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/13 13:24
29	0	rtcvd and ono and (applied adj materials).asn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/13 13:26
36	1	ono and (cluster adj tool) and (applied adj materials).asn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/13 13:27
43	11028	multichamber ((plural multi multiple several) adj chamber)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/13 13:28
50	78	ono and (multichamber ((plural multi multiple several) adj chamber))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/13 13:29
57	395	(rapid adj thermal) adj2 (CVD (chemical vapo\$1r deposit\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/13 13:31
64	1	(ono and (multichamber ((plural multi multiple several) adj chamber))) and ((rapid adj thermal) adj2 (CVD (chemical vapo\$1r deposit\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/13 13:35
78	2	5836772.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/13 14:23
85	12	ono and (((rapid adj thermal) adj2 (CVD (chemical vapo\$1r deposit\$3)))) near15 (nitride SiN ("Si.sub.3" adj "N.sub.4") Si3N4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/13 14:29

71	51	((rapid adj thermal) adj2 (CVD (chemical vapor deposit\$3))) near15 (nitride SiN ("Si.sub.3" adj "N.sub.4") Si3N4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/13 14:37
92	39	((rapid adj thermal) adj2 (CVD (chemical vapor deposit\$3))) near15 (nitride SiN ("Si.sub.3" adj "N.sub.4") Si3N4)) not ono	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/13 15:08
99	11848	(cluster adj tool) (multichamber ((plural multi multiple several) adj chamber))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/13 15:09
113	2	(ono and ((cluster adj tool) (multichamber ((plural multi multiple several) adj chamber)))) and ((rapid adj thermal) adj2 (CVD (chemical vapor deposit\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/13 15:09
106	94	ono and ((cluster adj tool) (multichamber ((plural multi multiple several) adj chamber)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/13 15:45
120	86560	gate adj2 (insulat\$3 isolat\$3 dielectric oxide dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/13 15:46
127	134	((cluster adj tool) (multichamber ((plural multi multiple several) adj chamber))) same (gate adj2 (insulat\$3 isolat\$3 dielectric oxide dioxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/13 15:47
134	40	((cluster adj tool) (multichamber ((plural multi multiple several) adj chamber))) near20 (gate adj2 (insulat\$3 isolat\$3 dielectric oxide dioxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/13 15:47